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# M66312P/FP

## 8-Bit LED Driver with Shift Register and Latched 3-State Outputs

REJ03F0178-0201 Rev.2.01 Mar 31, 2008

## **Description**

M66312 is a LED array driver having a 8-bit serial input and parallel output shiftregister function with 3-state output latch.

This product guarantees the output electric current of 16 mA which is sufficient for LED drive, capable of flowing 8 bits continuously at the same time, and use either of cathode common LED and anode common LED.

In addition, as this product has been designed in complete CMOS, power consumption can be greatly reduced when compared with conventional BIPOLAR or Bi-CMOS products.

## **Features**

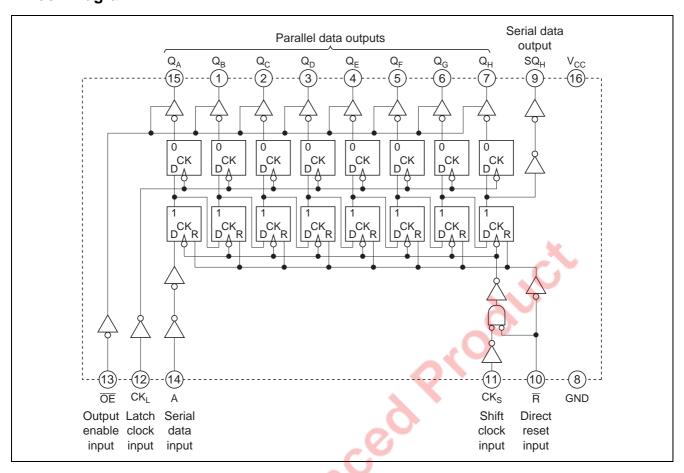
- High output current  $I_{OL} = 16 \text{ mA}$ ,  $I_{OH} = -16 \text{ mA}$
- High speed (clock frequency): 30 MHz (typ)  $(C_L = 50 \text{ pF}, V_{CC} = 5 \text{ V})$
- Low power dissipation: 20 μW/package (max)
   (V<sub>CC</sub> = 5 V, Ta = 25°C, quiescent state)
- 3-state output (except serial data output)
- Wide operating temperature range:  $Ta = -40 \text{ to } +85^{\circ}\text{C}$

## **Application**

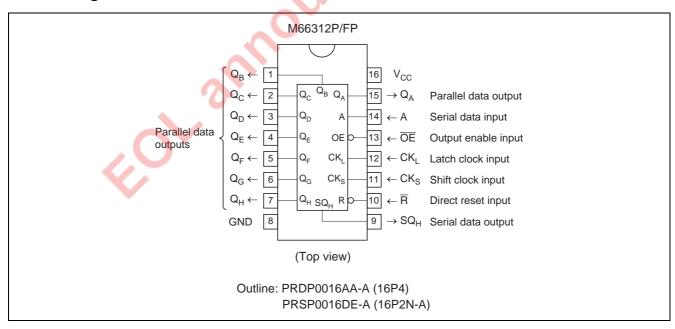
LED array drive of PRINTER

LED array drive of BUTTON TELEPHONE

## **Block Diagram**



## **Pin Arrangement**



## **Functional Description**

As M66312 uses silicon gate CMOS process, it realizes high-speed and high-output currents sufficient for LED drive while maintaining low power consumption and allowance for high noises.

Each bit of a shiftregister consists of two flip-flops having independent clocks for shifting and latching.

As for clock input, shift clock input  $CK_S$  and latch clock input  $CK_L$  are independent from each other, shift and latch operations being made when "L" changes to "H".

Serial data input A is the data input of the first-step shiftregister and the signal of A shifts shiting registers one by one when a pulse is impressed to CK<sub>S</sub>. When A is "H", the signal of "H" shifts. When A is "L", the signal of "L" shifts.

When the pulse is impressed to  $CK_L$ , the contents of the shifting register at that time are stored in a latching register, and they appear in the output from  $Q_A$  through  $Q_H$  are 3-state outputs.

To extend the number of bits, serial data output SQ<sub>H</sub> is used to output the 8-bit of the shift register.

By connecting CK<sub>S</sub> and CK<sub>L</sub>, the shift register state delayed by 1 clock cycle is output at Q<sub>A</sub> through Q<sub>H</sub>.

When reset input  $\overline{R}$  is low, shift register and  $SQ_H$  will be reset. To reset  $Q_A$  through  $Q_H$  to low-level,  $CK_L$  must be changed from low-level to high-level after the shift register is reset by  $\overline{R}$ .

When output-enable input  $\overline{OE}$  is high,  $Q_A$  through  $Q_H$  will become high impedance state, but  $SQ_H$  is not changed.

Even if  $\overline{OE}$  is changed, shift operation is not affected.

## Function Table (Note)

		Input				Parallel Data Output						Serial Data			
Operation Mode		R	CKs	CKL	Α	ŌĒ	$Q_A$	Q <sub>B</sub>	$Q_{C}$	$Q_D$	Q <sub>E</sub>	$Q_F$	$Q_G$	Q <sub>H</sub>	Output SQ <sub>H</sub>
Reset	Shift t1	L	Х	Х	Х	L	$Q_A^0$	Q <sub>B</sub> <sup>0</sup>	Q <sub>C</sub> <sup>0</sup>	$Q_D^0$	$Q_{E^0}$	Q <sub>F</sub> <sup>0</sup>	$Q_G^0$	Q <sub>H</sub> <sup>0</sup>	L
	Latch t2	Х	Х	<b>↑</b>	Х	L	L	L /	L	L	L	L	L	L	L
Shift	Shift t1	Н	1	Х	Н	L	$Q_A^0$	Q <sub>B</sub> <sup>0</sup>	Q <sub>C</sub> <sup>0</sup>	$Q_D^0$	Q <sub>E</sub> 0	Q <sub>F</sub> <sup>0</sup>	$Q_G^0$	Q <sub>H</sub> <sup>0</sup>	$q_G^0$
latch	Latch t2	Н	Х	<b>↑</b>	Х	L	Н	q <sub>A</sub> <sup>0</sup>	q <sub>B</sub> <sup>0</sup>	q <sub>C</sub> <sup>0</sup>	$q_D^0$	q <sub>E</sub> 0	q <sub>F</sub> 0	$q_G^0$	$q_G^0$
operation	Shift t1	Н	1	Х	L	L	$Q_A^0$	Q <sub>B</sub> 0	Q <sub>C</sub> <sup>0</sup>	$Q_D^0$	$Q_{E^0}$	Q <sub>F</sub> <sup>0</sup>	$Q_G^0$	Q <sub>H</sub> <sup>0</sup>	$q_G^0$
	Latch t2	Н	Х	<b>↑</b>	Х	L	L	$q_A^0$	$q_B^0$	q <sub>C</sub> <sup>0</sup>	$q_D^0$	q <sub>E</sub> <sup>0</sup>	q <sub>F</sub> <sup>0</sup>	$q_G^0$	$q_G^{0}$
3 state		Х	Х	Х	Х	Н	Z	Z	Z	Z	Z	Z	Z	Z	$q_H$

## Note

- 1: Change from low-level to high-level
- Q0: Output state Q before CKL changed
- X: Irrelevant
- q0: Contents of shift register before CKs changed
- q: Contents of shift register
- t<sub>1</sub>, t<sub>2</sub>: t<sub>2</sub> is set after t<sub>1</sub> is set
- Z: High impedance

## **Absolute Maximum Ratings**

 $(Ta = -40 \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted})$ 

Item		Symbol	Ratings	Unit	Conditions
Supply voltage		V <sub>CC</sub>	−0.5 to +7.0	V	
Input voltage		Vı	$-0.5$ to $V_{CC} + 0.5$	V	
Output voltage		Vo	-0.5 to V <sub>CC</sub> + 0.5	V	
Input protection diode current		I <sub>IK</sub>	-20	mA	$V_I < 0 V$
			20		$V_{I} > V_{CC}$
Output parasitic diode current	Output parasitic diode current		-20	mA	V <sub>O</sub> < 0 V
			20		Vo > Vcc
Output current per output pin	$\overline{Q}_A$ to $\overline{Q}_H$	lo	±35	mA	
	SQ <sub>H</sub>		±25		
Supply/GND current		Icc	±132	mA	V <sub>CC</sub> , GND
Power dissipation		Pd	500	mW	(Note)
Storage temperature range		Tstg	-65 to +150	°C	*

Note: M66312FP; Ta = -40 to +70°C, Ta = 70 to 85°C are derated at -6 mW/°C.

## **Recommended Operating Conditions**

 $(Ta = -40 \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted})$ 

				Limits		
Item		Symbol	Min	Тур	Max	Unit
Supply voltage		V <sub>CC</sub>	4.5	5	5.5	V
Input voltage	Vı	0	_	V <sub>cc</sub>	V	
Output voltage		Vo	0	_	V <sub>cc</sub>	V
Operating temperature range	Topr	-40	_	+85	°C	
Input rising and falling time	$V_{CC} = 4.5 \text{ V}$	tr, tf	0	_	500	ns
	$V_{CC} = 5.5 \text{ V}$		0	_	400	

## **Electrical Characteristics**

 $(V_{CC} = 4.5 \text{ to } 5.5\text{V}, \text{ unless otherwise noted})$ 

		Limits							
	Sym	Т	a = 25°C	;	Ta = -40	to +85°C			
Item	bol	Min	Тур	Max	Min	Max	Unit	Conditions	
High-level input voltage	V <sub>IH</sub>	0.70× V <sub>CC</sub>	_	_	0.70×V <sub>CC</sub>	_	V	$V_0 = 0.1 \text{ V}, V_0$ $ I_0  = 20  \mu\text{A}$	<sub>cc</sub> -0.1 V
Low-level Input voltage	V <sub>IL</sub>	_	_	0.30×V <sub>CC</sub>	_	0.30×V <sub>CC</sub>	V	$V_{O} = 0.1 \text{ V}, V_{O}$ $ I_{O}  = 20  \mu\text{A}$	<sub>cc</sub> -0.1 V
High-level output	V <sub>OH</sub>	V <sub>CC</sub> -0.1	_	_	V <sub>CC</sub> -0.1	_	V	$V_{I}=V_{IH},V_{IL}$	$I_{OH} = -20 \mu A$
voltage $Q_A$ to $Q_H$		3.70 <sup>(note)</sup>	_	_	3.55 <sup>(note)</sup>	_		$V_{CC} = 4.5 \text{ V}$	$I_{OH} = -16 \text{ mA}$
High-level output	V <sub>OH</sub>	V <sub>CC</sub> -0.1	_	_	V <sub>CC</sub> -0.1	_	V	$V_{I}=V_{IH},V_{IL}$	$I_{OH} = -20 \ \mu A$
voltage SQ <sub>H</sub>		4.0		_	3.9	_		$V_{CC} = 4.5 \text{ V}$	$I_{OH} = -4 \text{ mA}$
Low-level output	V <sub>OL</sub>	1		0.1	_	0.1	V	$V_{I} = V_{IH},  V_{IL}$	$I_{OL}=20\;\mu A$
voltage Q <sub>A</sub> to Q <sub>H</sub>				0.7 <sup>(note)</sup>	_	0.85 <sup>(note)</sup>		$V_{CC} = 4.5 \text{ V}$	$I_{OL} = 16 \text{ mA}$
Low-level output	V <sub>OL</sub>			0.1	_	0.1	V	$V_I = V_{IH}, \ V_{IL}$	$I_{OL}=20~\mu A$
voltage SQ <sub>H</sub>				0.4	_	0.5		$V_{CC} = 4.5 \text{ V}$	$I_{OL} = 4 \text{ mA}$
High-level input current	Іін	_	_	0.1	_	1.0	μА	$V_I = V_{CC}, V_{CC}$	= 5.5 V
Low-level input current	I <sub>IL</sub>	_	_	-0.1	_	-1.0	μΑ	$V_I = GND, V_{CO}$	c = 5.5 V
Off state high- level output current Q <sub>A</sub> to Q <sub>H</sub>	l <sub>OZH</sub>	_	_	1.0	5	10.0	μА	$\begin{aligned} V_I &= V_{IH}, \ V_{IL} \\ V_{CC} &= 5.5 \ V \end{aligned}$	$V_O = V_{CC}$
Off state low- level output current Q <sub>A</sub> to Q <sub>H</sub>	I <sub>OZL</sub>	_	_	-1.0	Co	-10.0	μА		$V_O = GND$
Quiescent supply current	Icc	_	_	4.0	_	40.0	μА	$V_I = V_{CC}$ , GND	$V_{CC} = 5.5 \text{ V}$

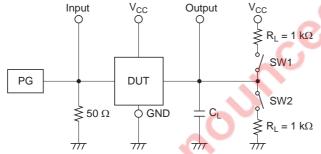
Note: Limits of single PIN operating state

## **Switching Characteristics**

 $(V_{CC} = 5 V)$ 

		Ta = 25°C			Ta = -40	to +85°C		
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions
Maximum clock frequency	f <sub>max</sub>	15	_		12	_	MHz	$C_L = 50 \text{ pF}$
Low-level to high-level and	t <sub>PLH</sub>		_	70	_	88	ns	$C_L = 15 pF$
high-level to low-level output propagation time CK <sub>S</sub> -SQ <sub>H</sub>	t <sub>PHL</sub>	_	_	70	_	88	ns	(Note)
$\begin{array}{c} \text{High-level to low-level} \\ \text{output propagation time } \overline{R} \text{-} \\ \text{SQ}_{\text{H}} \end{array}$	t <sub>PHL</sub>	_	_	60	_	76	ns	
Low-level to high-level and	t <sub>PLH</sub>	_	_	60	_	76	ns	$C_L = 50 pF$
high-level to low-level output propagation time CK <sub>L</sub> -Q <sub>A</sub> to Q <sub>H</sub>	t <sub>PHL</sub>	_	_	60	_	76	ns	(Note)
Output disable time from	t <sub>PLZ</sub>	_	_	50	_	64	ns	$C_L = 5 pF$
low-level and high-level <del>OE</del> -Q <sub>A</sub> to Q <sub>H</sub>	t <sub>PHZ</sub>	_	_	50	_	64	ns	(Note)
Output enable time to low-	t <sub>PZL</sub>	_	_	56		70	ns	$C_L = 50 pF$
level and high-level $\overline{\text{OE}}$ -Q <sub>A</sub> to Q <sub>H</sub>	t <sub>PZH</sub>	_	_	56	01	70	ns	(Note)

Note: Test Circuit



Item	SW1	SW2
t <sub>PLH</sub> , t <sub>PHL</sub>	Open	Open
t <sub>PLZ</sub>	Close	Open
t <sub>PHZ</sub>	Open	Close
t <sub>PZL</sub>	Close	Open
t <sub>PZH</sub>	Open	Close
₹PZH	Open	Ciose

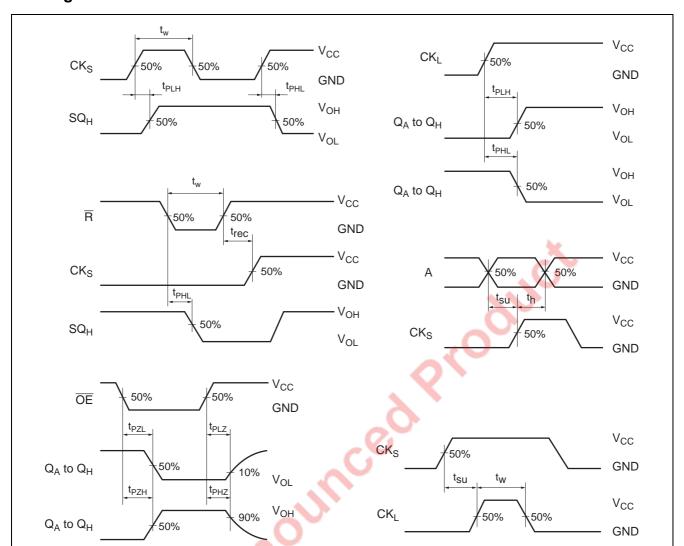
- (1) The pulse generator (PG) has the following characteristics (10% to 90%): tr = 6 ns, tf = 6 ns
- (2) The capacitance C<sub>L</sub> includes stray wiring capacitance and the probe input capacitance.

# **Timing Requirements**

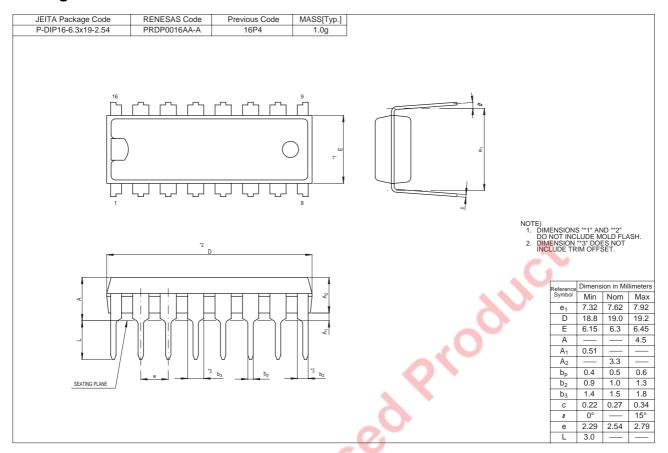
 $(V_{CC} = 5 V)$ 

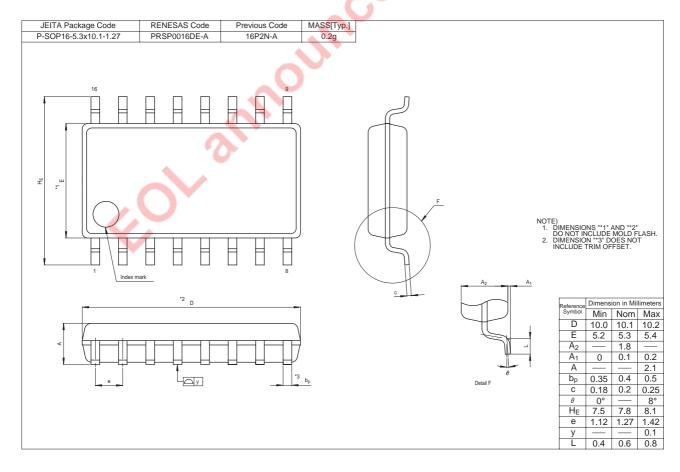
				Limits				
		Ta = 25°C			Ta = -40	to +85°C		
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions
CK <sub>S</sub> , CK <sub>L</sub> , R pulse width	t <sub>w</sub>	32	_	_	40	_	ns	
A setup time with respect to CK <sub>S</sub>	t <sub>su</sub>	40	_	_	50	_	ns	
CK <sub>S</sub> setup time with respect to CK <sub>L</sub>	t <sub>su</sub>	40	_	_	50	_	ns	
A hold time with respect to CK <sub>S</sub>	t <sub>h</sub>	10	_	_	10	_	ns	
R recovery time with respect to CK <sub>S</sub>	t <sub>rec</sub>	20	_	_	26	_	ns	

## **Timing Chart**



## **Package Dimensions**





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